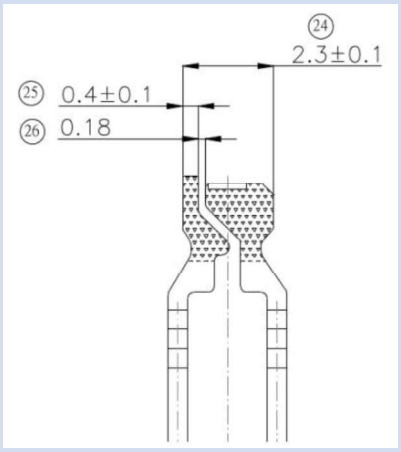
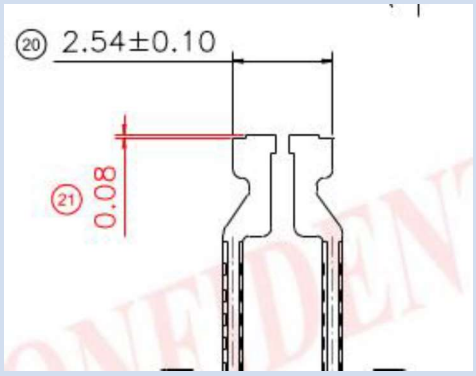
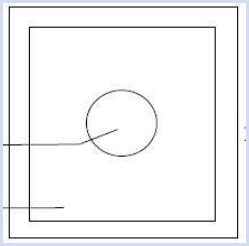
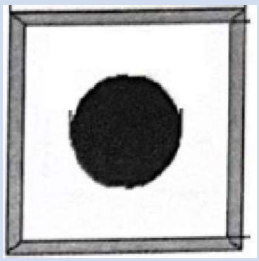
支架外觀對比外觀比較
leadframeappearance comparison

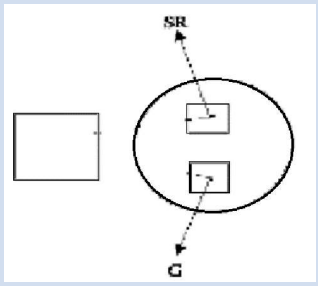
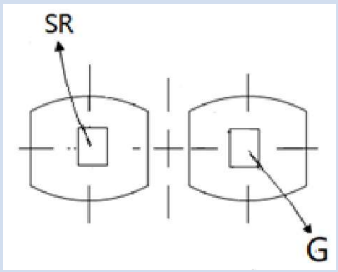
Now	After
	

晶片外觀對比外觀比較
chipappearance comparison

Now	After
	
photoelectricity (now)	photoelectricity (after)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F=20 mA		1.82	2.00	V
Reverse Voltage	V_R	I_R=10 μA	5			V
Luminous Intensity	Iv	I_F=20 mA	10.0	※		mcd
Wavelength	λp/λd	I_F=20 mA		655/640		nm
Spectrum Width of Half Value	△λ	I_F=20 mA		20		nm

参数	符号		条件	Min	Typ	Max	单位
正向电压	V_{f1}		I_f= 20mA	1.90		2.20	V
	V_{f2}		I_f= 10μA	1.30		1.60	V
反向电流	I_r		V_r=-10V	0		2.0	μA
主波长	λ_d		I_f=20mA	638		645	nm
半高宽	Δλ		I_f=20mA		20		nm
光强等级	IV	A1	I_f=20mA	14		22	mcd
		A2		19		27	
		A3		24		32	

位置position

Now	After